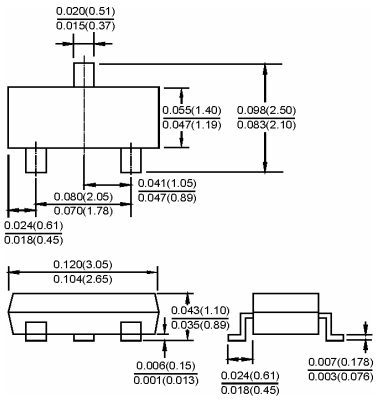
2SA1162

SOT-23 Bipolar Transistor(PNP)

1. BASE
2. EMITTER
3. COLLECTOR

SOT-23



Dimensions in inches and (millimeters)

Features

- ✧ **Low noise: NF=1dB(Typ.)10dB(Max.)**
- ✧ **Complementary to 2SC2712**
- ✧ **Small package**

MAXIMUM RATINGS (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-50	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current -Continuous	-150	mA
P_C	Collector Power Dissipation	150	mW
T_J	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55-125	℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-100μA,I_E=0	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA,I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-100μA,I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-50V,I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-5V,I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=-6V,I_C=-2mA	70		400	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-100mA,I_B=-10mA			-0.3	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-1mA	80			MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz			7	pF
Noise figure	NF	V_{CE}=-6V,I_C=0.1mA,f=1KHz, Rg=10KΩ			10	dB

CLASSIFICATION OF h_{FE}

Rank	O	Y	GR(G)
Range	70-140	120-240	200-400
Marking	SO	SY	SG

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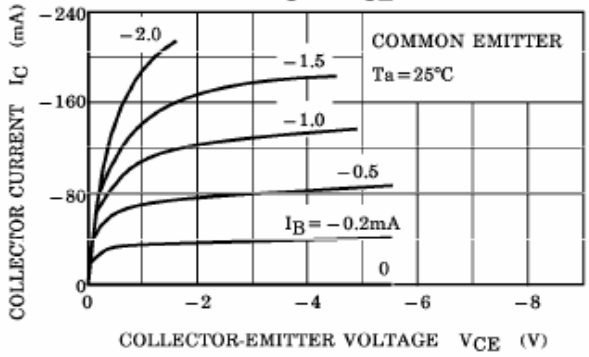
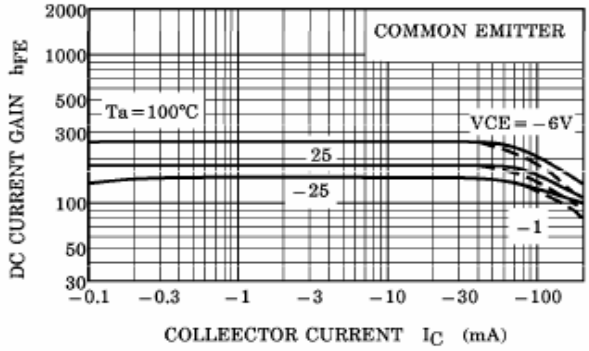
Typical Characteristics

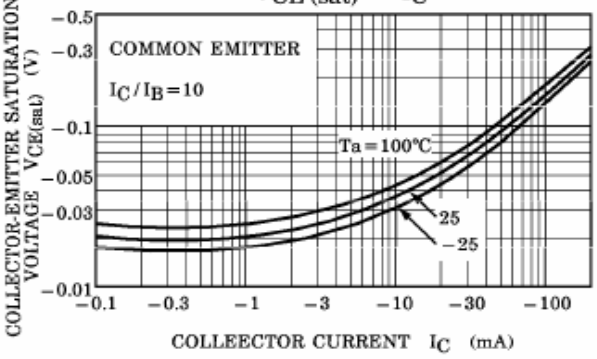
$I_C - V_{CE}$



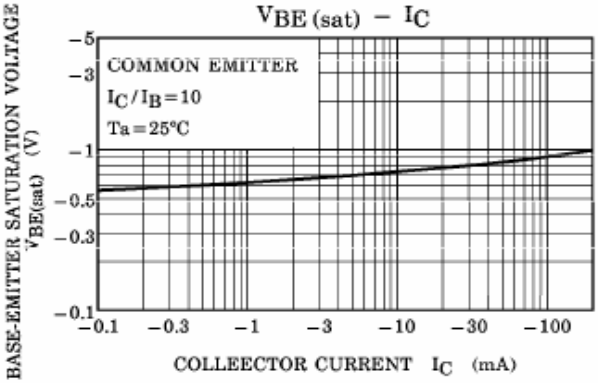
$h_{FE} - I_C$



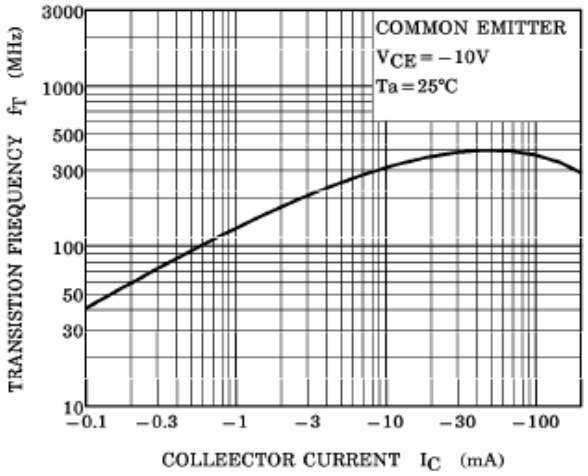
$V_{CE(sat)} - I_C$



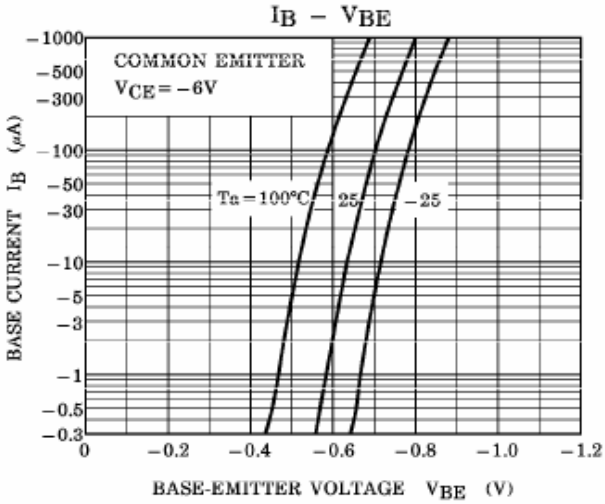
$V_{BE(sat)} - I_C$



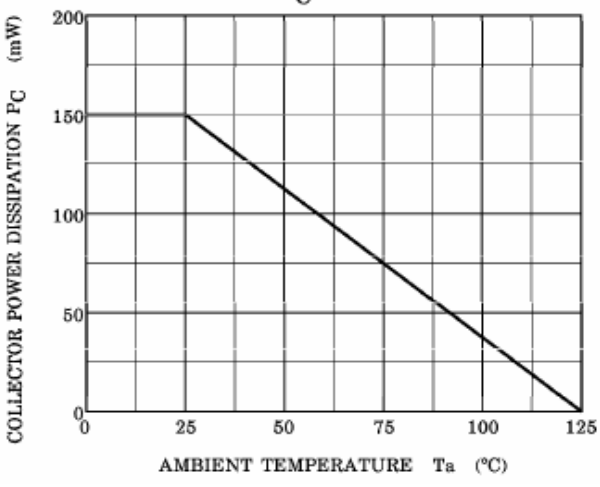
$f_T - I_C$



$I_B - V_{BE}$



$P_C - Ta$



Package	Reel	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)
SOT-23	3000pcs	7inch	45,000pcs	203×203×195	180,000pcs	438×438×220